

## $\mu$ PD5756T6N

# SiGe BiCMOS Integrated Circuit Wide Band LNA IC with Through Function

R09DS0026EJ0100 Rev.1.00 Oct 04, 2011

#### **DESCRIPTION**

The  $\mu$ PD5756T6N is a low noise wideband amplifier IC with the through function mainly designed for the digital TV application. This IC exhibits low noise figure and low distortion characteristics.

This IC is manufactured using our latest SiGe BiCMOS process that shows superior high frequency characteristics.

#### **FEATURES**

• Low voltage operation :  $V_{CC} = 3.1 \text{ to } 3.5 \text{ V } (3.3 \text{ V TYP.})$ 

• Low current consumption :  $I_{CC}1 = 25 \text{ mA TYP.}$  @ $V_{CC} = 3.3 \text{ V (LNA-mode)}$ 

:  $I_{CC}2 = 1 \mu A MAX$ . @ $V_{CC} = 3.3 V$  (Bypass-mode)

• Operation frequency : f = 40 to 1000 MHz

• Low noise : NF = 3.2 dB TYP. @f = 1.000 MHz (LNA-mode)

• Low distortion :  $IIP_3 = +9 \text{ dBm TYP}$ . @f1 = 500 MHz, f2 = 505 MHz (LNA-mode)

Low insertion loss : L<sub>ins</sub> = 1.7 dB TYP. @f = 1 000 MHz (Bypass-mode)
 High-density surface mounting : 6-pin plastic TSON (T6N) package (1.5 × 1.5 × 0.37 mm)

#### **APPLICATIONS**

• Low noise amplifier for the digital TV system, etc.

### ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPD5756T6N-E2	μPD5756T6N-E2-A	6-pin plastic	C4C	Embossed tape 8 mm wide
		TSON (T6N)		Pin 1, 6 face the perforation side of the tape
		(Pb-Free)		Qty 3 kpcs/reel

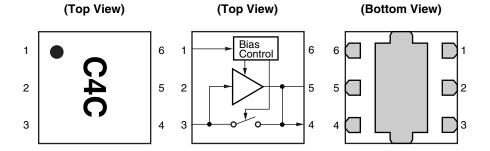
**Remark** To order evaluation samples, please contact your nearby sales office.

Part number for sample order: μPD5756T6N



Observe precautions when handling because these devices are sensitive to electrostatic discharge.

## PIN CONNECTIONS, MARKING AND INTERNAL BLOCK DIAGRAM



Pin No	Pin Name
1	$V_{cont}$
2	GND
3	INPUT
4	OUTPUT
5	Load
6	V <sub>CC</sub>

Remark Exposed pad: GND

#### **ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Conditions		Ratings	Unit
Supply Voltage	V <sub>CC</sub>	T <sub>A</sub> = +25°C		4.0	V
Mode Control Voltage	V <sub>cont</sub>	T <sub>A</sub> = +25°C		4.0	V
Total Power Dissipation	P <sub>tot</sub>	$T_A = +85^{\circ}C$ N	lote	300	mW
Operating Ambient Temperature	T <sub>A</sub>			-40 to +85	°C
Storage Temperature	T <sub>stg</sub>			-55 to +150	°C
Input Power	P <sub>in</sub>	T <sub>A</sub> = +25°C,		+15	dBm
		$Z_S = Z_L = 75 \Omega$			

Note: Mounted on double-sided copper-clad  $50 \times 50 \times 1.6$  mm epoxy glass PWB

## RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	$V_{CC}$	3.1	3.3	3.5	>
Mode Control Voltage (H)	V <sub>cont (H)</sub>	1.0		$V_{CC}$	V
Mode Control Voltage (L)	V <sub>cont (L)</sub>	-0.1	= (	0.4	V
Operating Frequency	f	40	-7	1 000	MHz
Operating Ambient Temperature	T <sub>A</sub>	-40	+25	+85	°C
Input Power (LNA-mode) Note	Pin		_	0	dBm
Input Power (Bypass-mode) Note	Pin	_	_	+10	dBm

Note:  $T_A = +25^{\circ}C$ ,  $Z_S = Z_L = 75 \Omega$ 

## ELECTRICAL CHARACTERISTICS 1 (DC Characteristics) $(T_A = +25^{\circ}C, V_{CC} = 3.3 \text{ V}, \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current 1	I <sub>cc</sub> 1	V <sub>cont</sub> = 3.3 V, No Signal (LNA-mode)	16	25	34	mA
Circuit Current 2	I <sub>CC</sub> 2	V <sub>cont</sub> = 0 V, No Signal (Bypass-mode)	-	0.01	1	μΑ
Mode Control Current 1	I <sub>cont</sub> 1	V <sub>cont</sub> = 3.3 V, No Signal (LNA-mode)	-	50	100	μΑ
Mode Control Current 2	I <sub>cont</sub> 2	V <sub>cont</sub> = 0 V, No Signal (Bypass-mode)	_	0.01	1	μΑ

## ELECTRICAL CHARACTERISTICS 2 (LNA-mode) ( $T_A = +25^{\circ}C$ , $V_{CC} = V_{cont} = 3.3 \text{ V}$ , $Z_S = Z_L = 75 \Omega$ , unless otherwise specified)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Power Gain 1	G <sub>P</sub> 1	$f = 40 \text{ MHz}, P_{in} = -20 \text{ dBm}$	10.5	13	15.5	dB
Power Gain 2	G <sub>P</sub> 2	$f = 1 000 \text{ MHz}, P_{in} = -20 \text{ dBm}$	10.5	13	15.5	dB
Noise Figure 1	NF1	f = 40 MHz, $Z_S$ = $Z_L$ = 50 Ω, excluded PCB and connector losses <b>Note</b>	ı	3.2	4.2	dB
Noise Figure 2	NF2	$f$ = 1 000 MHz, $Z_S$ = $Z_L$ = 50 $Ω$ , excluded PCB and connector losses Note	-	3.2	4.2	dB
Input Return Loss 1	RL <sub>in</sub> 1	f = 40 MHz, P <sub>in</sub> = –20 dBm	7	9	-	dB
Input Return Loss 2	RL <sub>in</sub> 2	f = 1 000 MHz, P <sub>in</sub> = –20 dBm	7	10	_	dB
Output Return Loss 1	RL <sub>out</sub> 1	f = 40 MHz, P <sub>in</sub> = –20 dBm	7	10	-	dB
Output Return Loss 2	RL <sub>out</sub> 2	f = 1 000 MHz, P <sub>in</sub> = –20 dBm	7	12	_	dB
Input 3rd Order Intercept Point	IIP <sub>3</sub>	f1 = 500 MHz, f2 = 505 MHz, P <sub>in</sub> = –20 dBm	+5	+9	ı	dBm

Note: Input PCB and connector losses: 0.03 dB (at 40 MHz), 0.10 dB (at 1 000 MHz)

## ELECTRICAL CHARACTERISTICS 3 (Bypass-mode) $(T_A = +25^{\circ}C, V_{CC} = 3.3 \text{ V}, V_{cont} = 0 \text{ V}, Z_S = Z_L = 75 \Omega, unless otherwise specified)$

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Insertion Loss 1	L <sub>ins</sub> 1	f = 40 MHz, P <sub>in</sub> = –10 dBm, excluded PCB and connector losses <b>Note</b>		0.5	1.5	dB
Insertion Loss 2	L <sub>ins</sub> 2	f = 1 000 MHz, P <sub>in</sub> = -10 dBm, excluded PCB and connector losses Note	<b>5</b>	1.7	2.5	dB
Input Return Loss 1	RL <sub>in</sub> 1	$f = 40 \text{ MHz}, P_{in} = -10 \text{ dBm}$	10	26	-	dB
Input Return Loss 2	RL <sub>in</sub> 2	f = 1 000 MHz, P <sub>in</sub> = -10 dBm	7	8	_	dB
Output Return Loss 1	RL <sub>out</sub> 1	$f = 40 \text{ MHz}, P_{in} = -10 \text{ dBm}$	10	25	-	dB
Output Return Loss 2	RL <sub>out</sub> 2	$f = 1000 \text{ MHz}, P_{in} = -10 \text{ dBm}$	7	8	ı	dB
Input 3rd Order Intercept Point	IIP <sub>3</sub>	f1 = 500 MHz, f2 = 505 MHz, P <sub>in</sub> = -5 dBm	+20	+29	-	dBm

Note: Input-output PCB and connector losses: 0.06 dB (at 40 MHz), 0.20 dB (at 1 000 MHz)

## STANDARD CHARACTERISTICS FOR REFERENCE 1 (LNA-mode) $(T_A = +25^{\circ}C, V_{CC} = V_{cont} = 3.3 \text{ V}, Z_S = Z_L = 75 \Omega, \text{ unless otherwise specified)}$

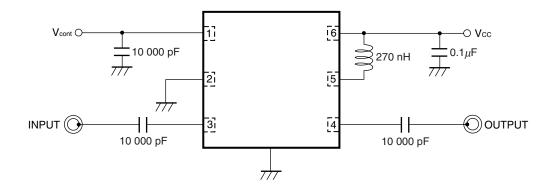
Parameter	Symbol	Test Conditions	Reference Value	Unit
Isolation 1	ISL1	f = 40 MHz, P <sub>in</sub> = –20 dBm	20	dB
Isolation 2	ISL2	f = 1 000 MHz, P <sub>in</sub> = –20 dBm	20	dB
Gain 1 dB Compression Output Power	P <sub>O (1 dB)</sub>	f = 500 MHz	+10	dBm

## STANDARD CHARACTERISTICS FOR REFERENCE 2 (Bypass-mode) $(T_A = +25^{\circ}C, V_{CC} = 3.3 \text{ V}, V_{cont} = 0 \text{ V}, Z_S = Z_L = 75 \Omega$ , unless otherwise specified)

Parameter	Symbol	Test Conditions	Reference Value	Unit
Gain 1 dB Compression Output	P <sub>O (1 dB)</sub>	f = 500 MHz	Note	dBm
Power				

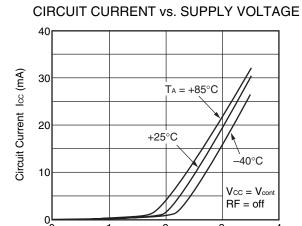
Note: The input-output power characteristic is not saturated up to +15 dBm of input power.

#### **TEST CIRCUIT**



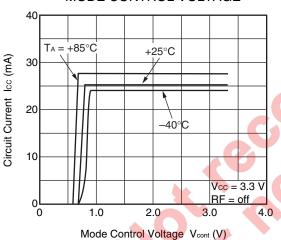


## TYPICAL CHARACTERISTICS 1 (DC Characteristics) $(T_A = +25^{\circ}C, unless otherwise specified)$

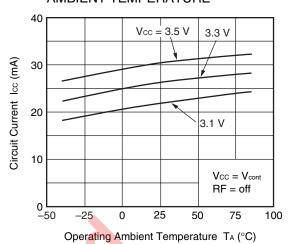


## CIRCUIT CURRENT vs. MODE CONTROL VOLTAGE

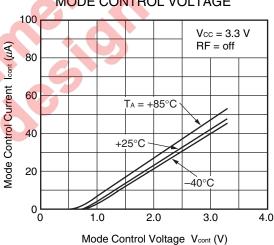
Supply Voltage Vcc (V)



## CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE

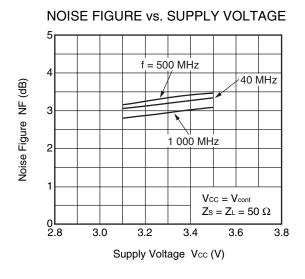


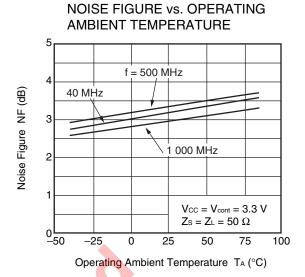
## MODE CONTROL CURRENT vs. MODE CONTROL VOLTAGE

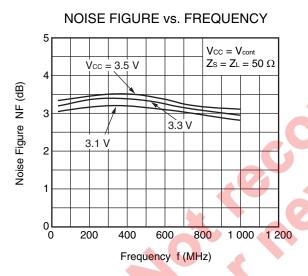


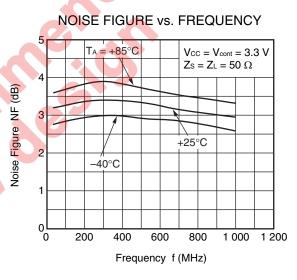
**Remark** The graphs indicate nominal characteristics.

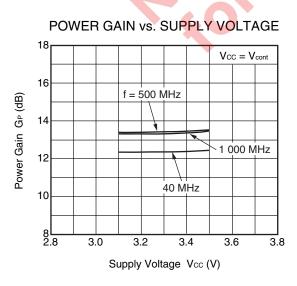
## TYPICAL CHARACTERISTICS 2 (LNA-mode) $(T_A = +25^{\circ}C, Z_S = Z_L = 75 \Omega, unless otherwise specified)$

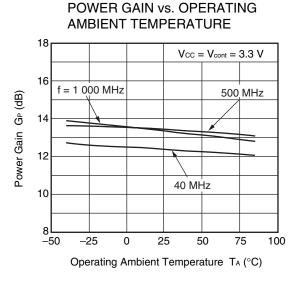




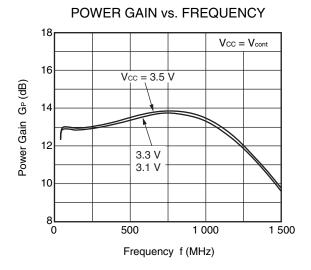


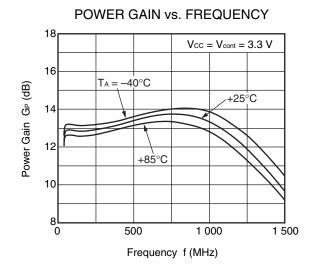


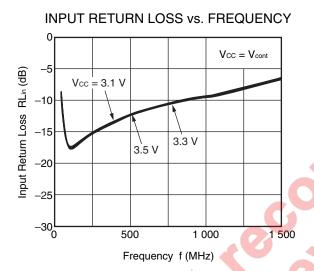


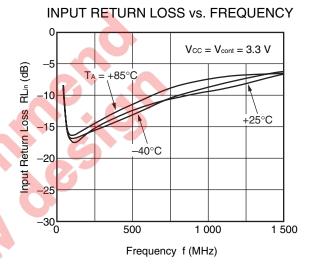


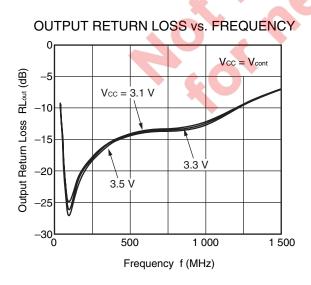
**Remark** The graphs indicate nominal characteristics.

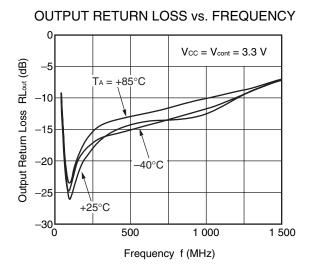




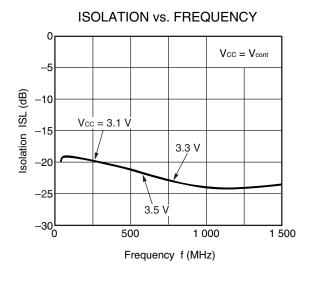


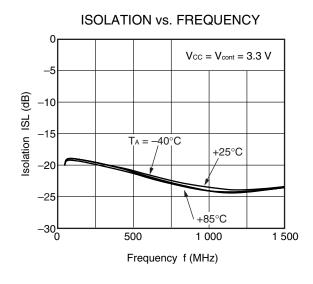


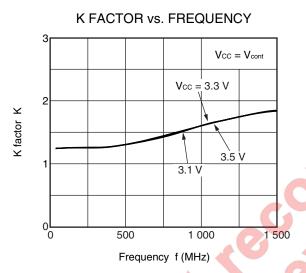


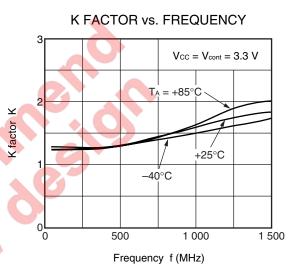


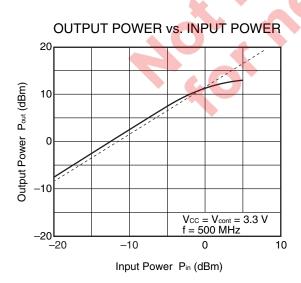
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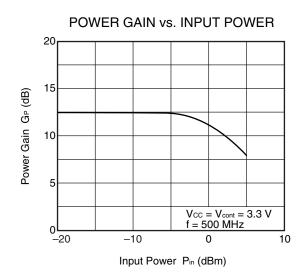




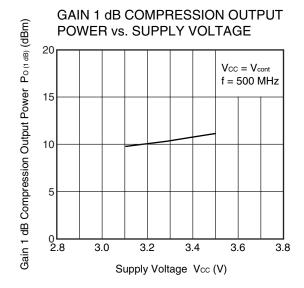


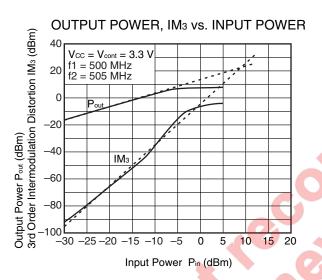




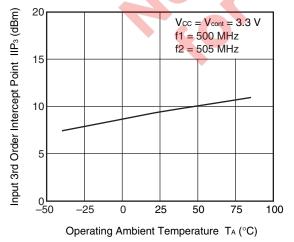


**Remark** The graphs indicate nominal characteristics.



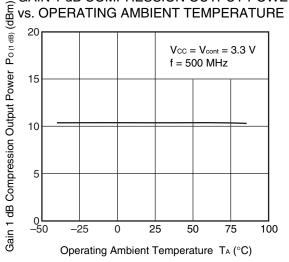


### INPUT 3RD ORDER INTERCEPT POINT vs. OPERATING AMBIENT TEMPERATURE

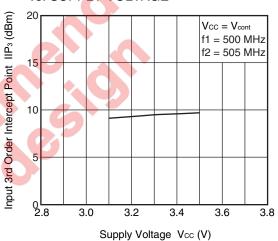


**Remark** The graphs indicate nominal characteristics.

### GAIN 1 dB COMPRESSION OUTPUT POWER vs. OPERATING AMBIENT TEMPERATURE



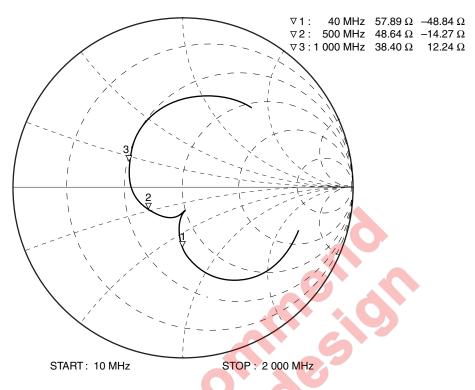
#### INPUT 3RD ORDER INTERCEPT POINT vs. SUPPLY VOLTAGE



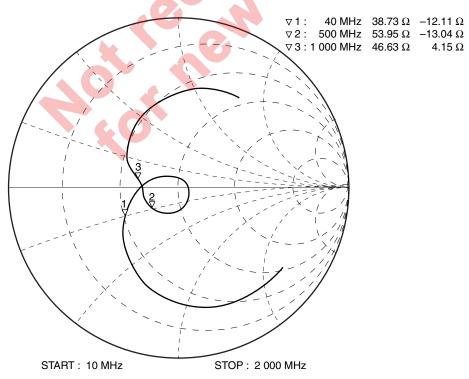
### S-PARAMETERS 1 (LNA-mode)

 $(T_A = +25^{\circ}C, V_{CC} = V_{cont} = 3.3 \text{ V}, Z_S = Z_L = 75 \Omega, \text{ monitored at connector on board})$ 

## S<sub>11</sub>-FREQUENCY



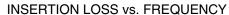
### S<sub>22</sub>-FREQUENCY

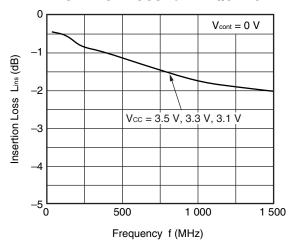


Remark The graphs indicate nominal characteristics.

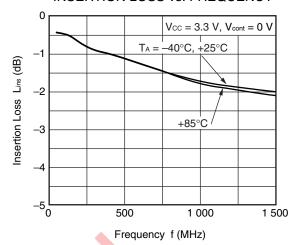
### TYPICAL CHARACTERISTICS 3 (Bypass-mode)

## $(T_A = +25^{\circ}C, Z_S = Z_L = 75 \Omega, unless otherwise specified)$

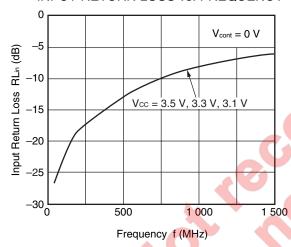




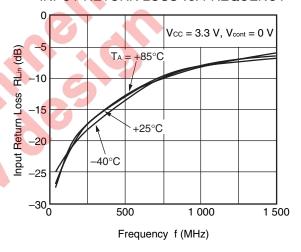
#### **INSERTION LOSS vs. FREQUENCY**



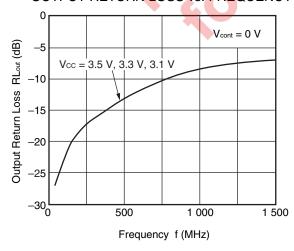
INPUT RETURN LOSS vs. FREQUENCY



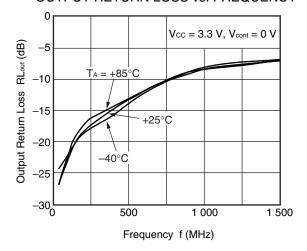
#### INPUT RETURN LOSS vs. FREQUENCY



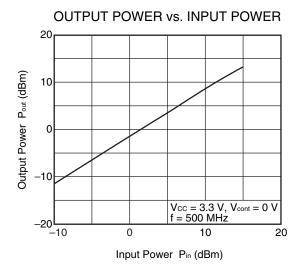
#### **OUTPUT RETURN LOSS vs. FREQUENCY**



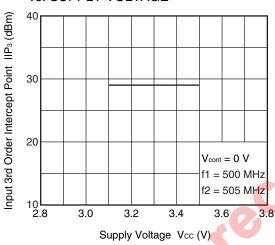
**OUTPUT RETURN LOSS vs. FREQUENCY** 



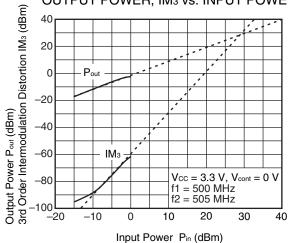
**Remark** The graphs indicate nominal characteristics.



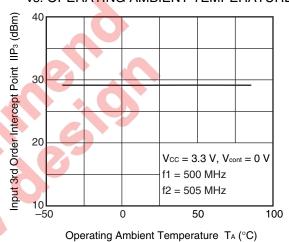




#### OUTPUT POWER, IM3 vs. INPUT POWER



## INPUT 3RD ORDER INTERCEPT POINT vs. OPERATING AMBIENT TEMPERATURE

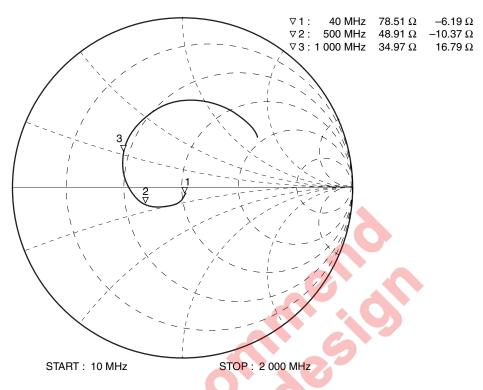


Remark The graphs indicate nominal characteristics.

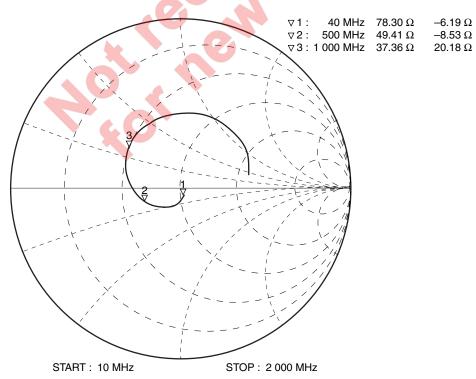
### S-PARAMETERS 2 (Bypass-mode)

 $(T_A = +25^{\circ}C, V_{CC} = 3.3 \text{ V}, V_{cont} = 0 \text{ V}, Z_S = Z_L = 75 \Omega, \text{ monitored at connector on board})$ 

## S<sub>11</sub>-FREQUENCY



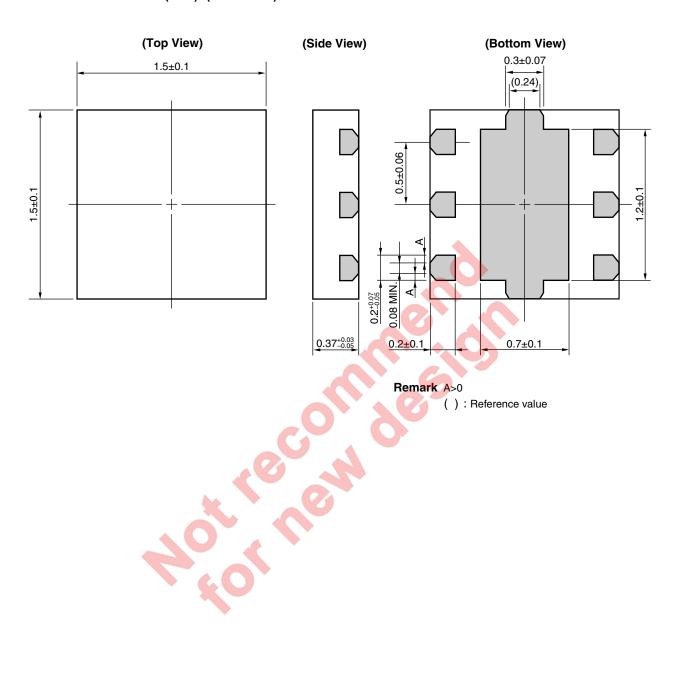
### S<sub>22</sub>-FREQUENCY



**Remark** The graphs indicate nominal characteristics.

### **PACKAGE DIMENSIONS**

### 6-PIN PLASTIC TSON (T6N) (UNIT: mm)



### **NOTES ON CORRECT USE**

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation).
- (3) All the ground terminals should be connected to the ground plane as close as possible.
- (4) The bypass capacitor should be attached to  $V_{CC}$  line.
- (5) Do not supply DC voltage to INPUT pin.

#### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	

#### **CAUTION**

Do not use different soldering methods together.



<b>Revision History</b>	Rev	ision	Hist	orv
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### μPD5756T6N Data Sheet

			Description			
Rev.	Date	Page	Summary			
1.00	Oct 04, 2011	_	First edition issued			



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